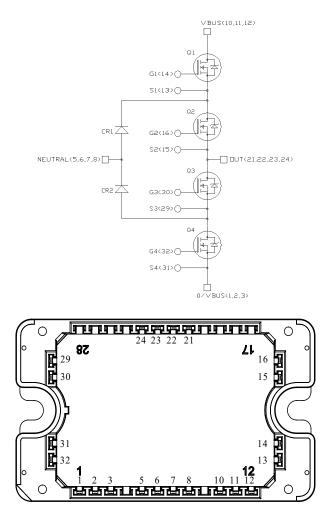


Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM120TLM50C3AG device is a 1200V/55A three level inverter silicon carbide (SiC) MOSFET power module.



Note:

- 1. All ratings at $T_J = 25$ °C, unless otherwise specified.
- 2. All multiple inputs and outputs must be shorted together: 1/2/3 ; 10/11/12 ; 5/6/7/8 ; 21/22/23/24

A CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

•

The following are the key features of MSCSM120TLM50C3AG device:

- SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
 - SiC Schottky Diode (CR1 and CR2)
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Low stray inductance
- High level of integration
- AIN substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120TLM50C3AG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Application

The following are the applications of MSCSM120TLM50C3AG device:

• Uninterruptible power supplies

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120TLM50C3AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of MSCSM120TLM50C3AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V _{DSS}	Drain-Source voltage	rce voltage		V
I _D	Continuous drain current	T _C = 25 °C	55	A
		T _C = 80 °C	44	
I _{DM}	Pulsed drain current		110	
V _{GSmax}	Gate-Source voltage		-10/25	V
R _{DS(on)}	Drain-Source ON resistance		50	mΩ
P _D	Power dissipation	T _C = 25 °C	245	W

The following table lists the electrical characteristics of MSCSM120TLM50C3AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V V _{DS} = 1200V			10	100	μA
R _{DS(on)}	Drain–Source on resistance	V _{GS} = 20V I _D = 40A	T _J = 25 °C T _J = 175 °C		40 64	50 —	mΩ
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 1 \text{ mA}$		1.8	2.7	—	V
I _{GSS}	Gate–Source leakage current	V _{GS} = 20V V _{DS} = 0V				150	nA

Table 1-2. Electrical Characteristics

Electrical Specifications

The following table lists the dynamic characteristics of MSCSM120TLM50C3AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V -		_	1990	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V		_	156	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	17	_	
Qg	Total gate charge	VGS = -5V/20V		_	137	_	nC
Qgs	Gate-Source charge	V _{Bus} = 800V		_	29	_	
Q _{gd}	Gate-Drain charge	I _D = 40A		_	31	_	
T _{d(on)}	Turn-on delay time	$V_{GS} = -5V/20V$ $T_{J} = 150 \ ^{\circ}C$	_	30	_	ns	
Tr	Rise time	V _{Bus} = 600V		_	40	_	
T _{d(off)}	Turn-off delay time	I _D = 40A		_	60	_	
Τ _f	Fall time	R _{Gon} = 10Ω R _{Goff} = 5.8Ω			20	_	
Eon	Turn-on energy	V _{GS} = -5V/20V	Т _Ј = 150 °С	_	0.8	_	mJ
Eoff	Turn-off energy	V _{Bus} = 600V I _D = 40A R _{Gon} = 10Ω R _{Goff} = 5.8Ω	TJ = 150 °C	-	0.53	_	
RGint	Internal gate resistance			_	1.2	_	Ω
R _{th} JC	Junction-to-case thermal	resistance		—	—	0.61	°C/W

Table 1-3. Dynamic Characteristics

The following table lists the body diode ratings and characteristics of MSCSM120TLM50C3AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V_{SD}	Diode forward voltage	V _{GS} = 0V		4		V
		I _{SD} = 40A				
t _{rr}	Reverse recovery time	I _{SD} = 40A		100		ns
Q _{rr}	Reverse recovery charge	$V_{GS} = -5V$		550		nC
I _{rr}	Reverse recovery current	V _R = 800V		13		A
		di _F /dt = 1000 A/µs				

1.2 CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the CR1 and CR2 SiC diode ratings and characteristics (per SiC diode) of MSCSM120TLM50C3AG device.

Table 1-5. CR ²	1 and CR2 SiC Diode	Ratings and	Characteristics
		r tatingo ana	enal actoriotiou

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
V _{RRM}	Peak repetitive reverse vo	oltage		—	—	1200	V
I _{RM}	Reverse leakage current	V _R = 1200 V	T _J = 25 °C	—	10	200	μA
			T _J = 175 °C	_	150	—	
I _F	DC forward current		T _C = 100 °C	-	30	—	A
V _F	Diode forward voltage	I _F = 30 A	T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C	_	2.1	—	
Q _C	Total capacitive charge	V _R = 600 V		—	130	—	nC
С	Total capacitance	f = 1 MHz		—	141	—	pF
		V _R = 400 V					
		f = 1 MHz		_	105	_	
		V _R = 800 V					
R _{thJH}	Junction-to-heatsink therr	nal resistance		_	_	0.9	°C/W

Electrical Specifications

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120TLM50C3AG device.

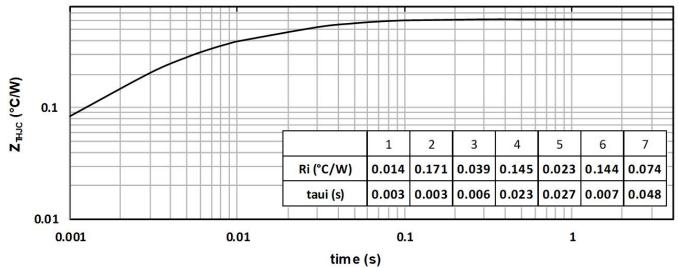
Symbol	Characteristic			Min.	Max.	Unit
V _{ISOL}	RMS isolation voltage, any termina	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			—	V
TJ	Operating junction temperature range			-40	175	°C
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _{Jmax} –25	
T _{STG}	Storage case temperature	Storage case temperature			125	
T _C	Operating case temperature			-40	125	
Torque	Mounting torque	Mounting torque To heatsink M4		2	3	N.m
Wt	Package weight			_	110	g

Table 1-6. Thermal and Package Characteristics

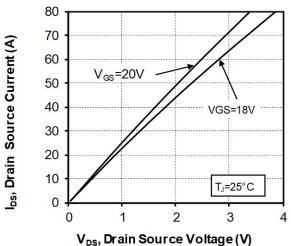
1.4 Typical SiC MOSFET Performance Curve (Per SiC MOSFET)

This section shows the typical SiC MOSFET performance curves of the MSCSM120TLM50C3AG device.

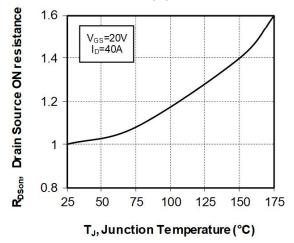


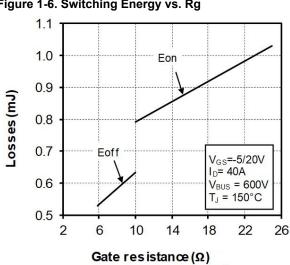


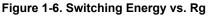
Electrical Specifications

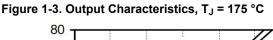












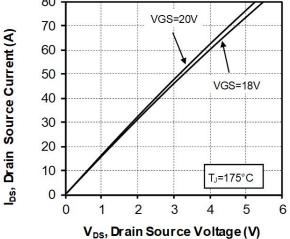


Figure 1-5. Transfer Characteristics

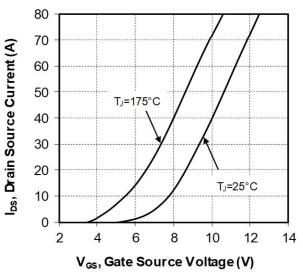
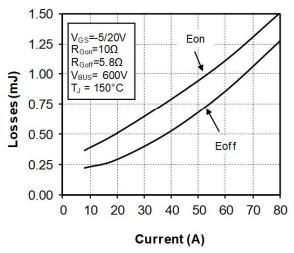


Figure 1-7. Switching Energy vs. Current



Electrical Specifications

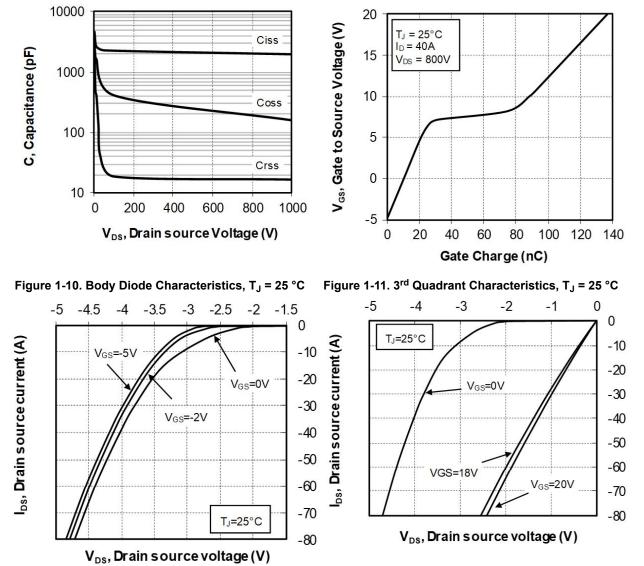
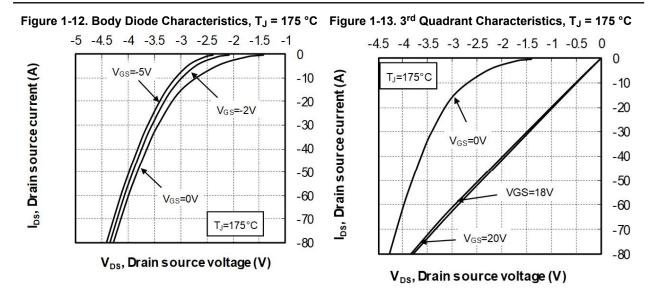
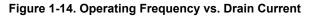


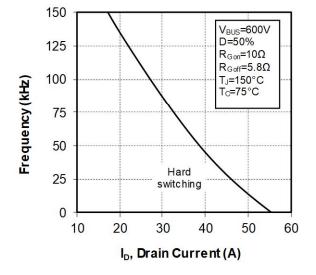
Figure 1-8. Capacitance vs. Drain Source Voltage

Figure 1-9. Gate Charge vs. Gate Source Voltage

Electrical Specifications



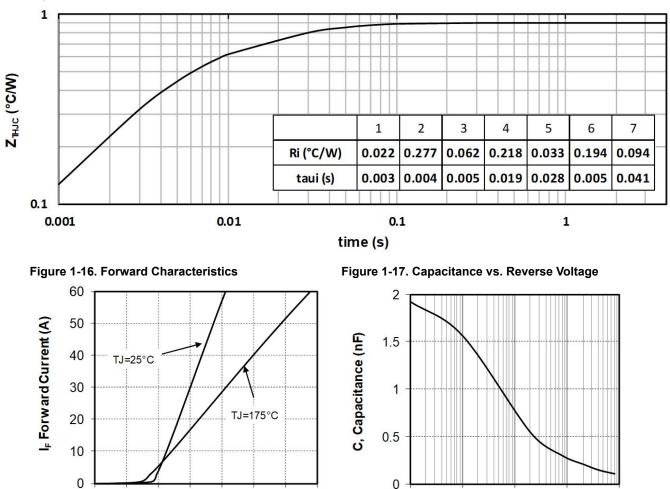




Electrical Specifications

1.5 Typical SiC Diode Performance Curves (Per SiC Diode)

This section shows the typical SiC diode performance curves of the MSCSM120TLM50C3AG device.





0

0.5

1

1.5

V_F Forward Voltage (V)

2

2.5

3

3.5

0.1

1

10

V_R Reverse Voltage

100

1000

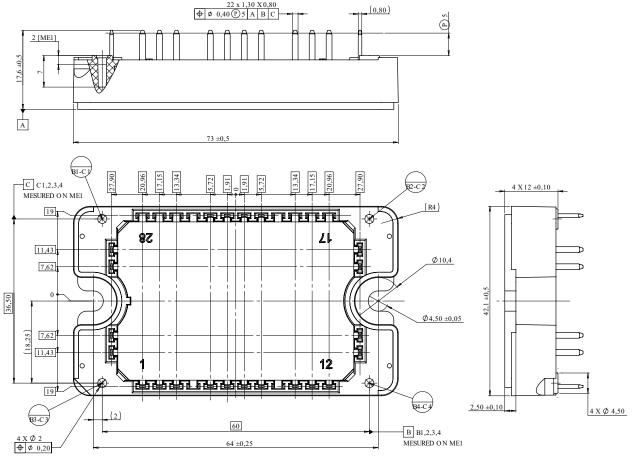
2. Package Specifications

The following section shows the package specification of the device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120TLM50C3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note AN3500A—Mounting instructions for SP1F and SP3F power modules.

3. Revision History

Revision	Date	Description
Α	12/2021	Initial Revision

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